

Nikolay Vostokov

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64
papers

279
citations

9
h-index

13
g-index

66
ext. papers

299
ext. citations

1.3
avg, IF

2.47
L-index

#	Paper	IF	Citations
64	Growth and photoluminescence of self-assembled islands obtained during the deposition of Ge on a strained SiGe layer. <i>Optical Materials</i> , 2005 , 27, 818-821	3.3	31
63	Low-energy photoluminescence of structures with GeSi/Si(001) self-assembled nanoislands. <i>JETP Letters</i> , 2002 , 76, 365-369	1.2	18
62	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 62-65	3.1	16
61	The elastic strain and composition of self-assembled GeSi islands on Si(001). <i>Thin Solid Films</i> , 2000 , 367, 171-175	2.2	13
60	On the role of tunneling in metal-semiconductor nanocontacts. <i>Journal of Experimental and Theoretical Physics</i> , 2004 , 99, 211-216	1	11
59	Transition from dome to pyramid shape of self-assembled GeSi islands. <i>Journal of Crystal Growth</i> , 2000 , 209, 302-305	1.6	11
58	Simulation of the Electron Transport in a Mott Diode by the Monte Carlo Method. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 2507-2510	2.9	10
57	Coherent effect of four XeCl laser beams on a surface. <i>Quantum Electronics</i> , 2000 , 30, 333-336	1.8	9
56	Study of correlation between the microstructure and phase inhomogeneities of Y-Ba-Cu-O epitaxial films and their DC and microwave properties. <i>Superconductor Science and Technology</i> , 1999 , 12, 908-911	3.1	9
55	Photoluminescence of self-assembled GeSi/Si(001) nanoislands of different shapes. <i>Physics of the Solid State</i> , 2004 , 46, 60-63	0.8	8
54	Influence of a predeposited Si _{1-x} Ge _x layer on the growth of self-assembled SiGe/Si(001) islands. <i>Physics of the Solid State</i> , 2005 , 47, 26	0.8	8
53	Si _{1-x} Ge _x /Si(001) relaxed buffer layers grown by chemical vapor deposition at atmospheric pressure. <i>Physics of the Solid State</i> , 2005 , 47, 42	0.8	8
52	Competition between the barrier and injection mechanisms of nonlinearity of the current-voltage characteristic in Mott-barrier detector diodes. <i>Journal of Applied Physics</i> , 2009 , 106, 043702	2.5	7
51	Analytical solution for charge-carrier injection into an insulating layer in the drift diffusion approximation. <i>Journal of Applied Physics</i> , 2008 , 104, 123708	2.5	7
50	Photoluminescence of Ge(Si)/Si(0 0 1) self-assembled islands in the near infra-red wavelength range. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 16, 467-472	3	7
49	Observation of laser-induced local modification of magnetic order in transition metal layers. <i>JETP Letters</i> , 2001 , 73, 192-196	1.2	7
48	Experimental Studies of the Frequency Dependence of the Low-Barrier Mott Diode Impedance. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 109-114	2.9	6

47	Electrical properties of metal-semiconductor nanocontacts. <i>Semiconductors</i> , 2004 , 38, 1047-1052	0.7	6
46	Photoluminescence of GeSi/Si(0 0 1) self-assembled islands with dome and hut shape. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 23, 416-420	3	6
45	Application of low-barrier metal-semiconductor-metal structures for the detection of microwave signals. <i>Technical Physics</i> , 2014 , 59, 1036-1040	0.5	5
44	The sandwich InGaAs/GaAs quantum dot structure for IR photoelectric detectors. <i>Semiconductors</i> , 2008 , 42, 99-103	0.7	5
43	Special features of the formation of Ge(Si) islands on the relaxed Si _{1-x} Gex/Si(001) buffer layers. <i>Semiconductors</i> , 2006 , 40, 229-233	0.7	5
42	Fabrication of Strain-Relaxed Si _{1-x} Gex/Si(001) Buffer Layers of Low Surface Roughness. <i>Russian Microelectronics</i> , 2005 , 34, 203-209	0.5	5
41	Study of Electrophysical Characteristics of pHEMT Heterostructures by the Methods of Impedance Spectroscopy. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1327-1332	2.9	4
40	Quantitative analysis of the elemental composition and electron concentration in AlGaIn/GaN heterostructures with a two-dimensional electron channel by means of SIMS and C-V profiling. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2012 , 76, 221-224	0.4	4
39	Sensing Microwave-Terahertz Detectors Based on Metal-Semiconductor-Metal Structures With Symmetrical I _V Characteristic. <i>IEEE Journal of the Electron Devices Society</i> , 2013 , 1, 76-82	2.3	4
38	Effect of B atoms on the properties of InAs quantum dots in the GaAs matrix. <i>Journal of Surface Investigation</i> , 2008 , 2, 514-517	0.5	4
37	Admittance and nonlinear capacitance of a multilayer metal-semiconductor structure. <i>Semiconductors</i> , 2008 , 42, 783-787	0.7	4
36	Synthesis of cyanoethyl chitosan derivatives. <i>Polymer Science - Series A</i> , 2006 , 48, 483-488	1.2	4
35	Influence of the germanium deposition rate on the growth and Photoluminescence of Ge(Si)/Si(001) self-assembled islands. <i>Physics of the Solid State</i> , 2005 , 47, 38	0.8	4
34	Development of contact scanning probe lithography methods for the fabrication of lateral nano-dimensional elements. <i>Nanotechnology</i> , 2000 , 11, 188-191	3.4	4
33	Detectors Based on Low-Barrier Mott Diodes and Their Characteristics in the 150-50 GHz Range. <i>Technical Physics Letters</i> , 2019 , 45, 239-241	0.7	3
32	Near-field microwave tomography of planar semiconductor microstructures. <i>Journal of Applied Physics</i> , 2017 , 122, 244505	2.5	3
31	Elastic strain and composition of self-assembled GeSi nanoislands on Si(001). <i>Semiconductors</i> , 2000 , 34, 6-10	0.7	3
30	Photoconductivity of InAs/GaAs structures with InAs nanoclusters in the near-infrared region. <i>Semiconductors</i> , 2010 , 44, 1464-1466	0.7	2

29	Picosecond kinetics of photoexcited carriers in gallium arsenide containing aluminum nanoclusters. <i>Semiconductors</i> , 2007 , 41, 909-913	0.7	2
28	Interference nanolithography with a UV laser. <i>Technical Physics</i> , 2004 , 49, 1191-1195	0.5	2
27	GeSi/Si(001) Structures with Self-Assembled Islands: Growth and Optical Properties 2005 , 333-351		2
26	Microwave detector diodes based on InGaAs/AlGaAs/GaAs heterostructures. <i>Journal of Applied Physics</i> , 2020 , 127, 044503	2.5	1
25	Analytical solution for the potential distribution in a stripe Schottky contact. <i>Journal of Applied Physics</i> , 2014 , 115, 244503	2.5	1
24	Electrical and structural parameters of YBCO films obtained by repeated growth cycles. <i>Technical Physics Letters</i> , 2011 , 37, 671-673	0.7	1
23	Comparative analysis of morphology and optical properties of GaN layers on sapphire. <i>Journal of Surface Investigation</i> , 2009 , 3, 718-720	0.5	1
22	Deposition of YBCO films on both sides of substrate by magnetron sputtering. <i>Technical Physics Letters</i> , 2010 , 36, 859-861	0.7	1
21	MOVPE of structures with aluminum nanocluster layers in a GaAs matrix. <i>Technical Physics Letters</i> , 2007 , 33, 444-446	0.7	1
20	Photoluminescence up to 1.6 μm of quantum dots with an increased effective thickness of the InAs layer. <i>Semiconductors</i> , 2008 , 42, 298-304	0.7	1
19	Effect of cation composition on the superconducting properties and on the microstructure of YBaCuO thin films. <i>Physics of the Solid State</i> , 2003 , 45, 2025-2030	0.8	1
18	Effect of the parameters of sapphire substrates on the crystalline quality of GaN layers. <i>Semiconductors</i> , 2005 , 39, 1	0.7	1
17	Fabrication and characterization of stress-free microbeams for MEMS applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1433-1437		1
16	Low-barrier Mott diodes with near-surface polarization-induced δ -doping. <i>Applied Physics Letters</i> , 2020 , 116, 013505	3.4	1
15	Simulation of the Response of a Low-Barrier Mott Diode to the Influence of Heavy Charged Particles from Outer Space. <i>Technical Physics Letters</i> , 2021 , 47, 305-308	0.7	1
14	Influence of the channel gate barrier height on the detection properties of a field-effect transistor in the microwave and terahertz ranges. <i>Technical Physics</i> , 2017 , 62, 765-772	0.5	0
13	Vertical Field-Effect Transistor with a Controlling GaAs-Based p δ Junction. <i>Semiconductors</i> , 2019 , 53, 1279-1281	0.7	
12	Terahertz signal detection in a short gate length field-effect transistor with a two-dimensional electron gas. <i>Journal of Applied Physics</i> , 2015 , 118, 204503	2.5	

- 11 Recharging dynamics of Al Nanoclusters in a GaAs matrix. *Journal of Surface Investigation*, **2012**, 6, 564-567
- 10 Diagnostics of cap layers in InAs(N) quantum-dot multilayer structures on GaAs(001), grown by metal-organic vapor-phase epitaxy. *Bulletin of the Russian Academy of Sciences: Physics*, **2007**, 71, 103-105^{0.4}
- 9 Solution of the problem of charge-carrier injection into an insulating layer under self-consistent boundary conditions at contacts. *Semiconductors*, **2008**, 42, 1309-1314 0.7
- 8 Optimization of the temperature mode of metal-organic chemical vapor deposition of the InAs(N) quantum dots on GaAs (001) with intense photoluminescence at 1.3 μm . *Semiconductors*, **2006**, 40, 449-453^{0.7}
- 7 A study of the properties of the structures with Al nanoclusters incorporated into the GaAs matrix. *Semiconductors*, **2005**, 39, 82 0.7
- 6 Special features in the synthesis and properties of thin Y-Ba-Cu-O high-temperature superconductor films free of secondary phases. *Technical Physics Letters*, **2001**, 27, 197-199 0.7
- 5 Investigation of inhomogeneities in thin films of high-temperature superconductors by scanning probe microscopy. *Technical Physics Letters*, **1999**, 25, 154-156 0.7
- 4 Modeling the Response of a Microwave Low-Barrier Uncooled Mott Diode to the Action of Heavy Ions of Outer Space and Femtosecond Laser Pulses. *Semiconductors*, **2021**, 55, 780 0.7
- 3 Microwave VoltImpedance Spectroscopy of Semiconductors. *Technical Physics*, **2020**, 65, 1859-1865 0.5
- 2 The sandwich InGaAs/GaAs quantum dot structure for IR photoelectric detectors **2010**, 42, 99
- 1 10.1007/s11453-008-3010-9 **2010**, 42, 298